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Details

Product Status	Obsolete
Core Processor	XC800
Core Size	8-Bit
Speed	86MHz
Connectivity	LINbus, SSI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	19
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	38-TFSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-38
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/saf-xc866l-2fri-bc

Summary of Features
XC866 Variant Devices

The XC866 product family features devices with different configurations and program memory sizes, temperature and quality profiles (Automotive or Industrial), offering cost-effective solution for different application requirements.

The configuration of LIN BSL for XC866 devices are summarized in **Table 1**.

Table 1 Device Configuration for LIN BSL

Device Name	LIN BSL Support
XC866	No
XC866L	Yes

The list of XC866 devices and their differences are summarized in **Table 2**.

Table 2 Device Summary

Device Type	Device Name	Power Supply (V)	P-Flash Size (Kbytes)	D-Flash Size (Kbytes)	ROM Size (Kbytes)	Quality Profile ¹⁾
Flash ²⁾	SAK-XC866*-4FRA	5.0	12	4	–	Automotive
	SAK-XC866*-4FRI	5.0	12	4	–	Industrial
	SAK-XC866*-2FRA	5.0	4	4	–	Automotive
	SAK-XC866*-2FRI	5.0	4	4	–	Industrial
	SAK-XC866*-1FRA	5.0	–	4	–	Automotive
	SAK-XC866*-1FRI	5.0	–	4	–	Industrial
	SAF-XC866*-4FRA	5.0	12	4	–	Automotive
	SAF-XC866*-4FRI	5.0	12	4	–	Industrial
	SAF-XC866*-2FRA	5.0	4	4	–	Automotive
	SAF-XC866*-2FRI	5.0	4	4	–	Industrial
	SAF-XC866*-1FRA	5.0	–	4	–	Automotive
	SAF-XC866*-1FRI	5.0	–	4	–	Industrial
	SAK-XC866*-4FRA 3V	3.3	12	4	–	Automotive
	SAK-XC866*-4FRI 3V	3.3	12	4	–	Industrial
	SAK-XC866*-2FRA 3V	3.3	4	4	–	Automotive
	SAK-XC866*-2FRI 3V	3.3	4	4	–	Industrial
	SAK-XC866*-1FRA 3V	3.3	–	4	–	Automotive

Summary of Features
Table 2 Device Summary

	SAK-XC866*-1FRI 3V	3.3	—	4	—	Industrial
	SAF-XC866*-4FRA 3V	3.3	12	4	—	Automotive
	SAF-XC866*-4FRI 3V	3.3	12	4	—	Industrial
	SAF-XC866*-2FRA 3V	3.3	4	4	—	Automotive
	SAF-XC866*-2FRI 3V	3.3	4	4	—	Industrial
	SAF-XC866*-1FRA 3V	3.3	—	4	—	Automotive
	SAF-XC866*-1FRI 3V	3.3	—	4	—	Industrial
ROM	SAK-XC866*-4RRA	5.0	—	4	16	Automotive
	SAK-XC866*-4RRI	5.0	—	4	16	Industrial
	SAK-XC866*-2RRA	5.0	—	4	8	Automotive
	SAK-XC866*-2RRI	5.0	—	4	8	Industrial
	SAF-XC866*-4RRA	5.0	—	4	16	Automotive
	SAF-XC866*-4RRI	5.0	—	4	16	Industrial
	SAF-XC866*-2RRA	5.0	—	4	8	Automotive
	SAF-XC866*-2RRI	5.0	—	4	8	Industrial
	SAK-XC866*-4RRA 3V	3.3	—	4	16	Automotive
	SAK-XC866*-4RRI 3V	3.3	—	4	16	Industrial
	SAK-XC866*-2RRA 3V	3.3	—	4	8	Automotive
	SAK-XC866*-2RRI 3V	3.3	—	4	8	Industrial
	SAF-XC866*-4RRA 3V	3.3	—	4	16	Automotive
	SAF-XC866*-4RRI 3V	3.3	—	4	16	Industrial
	SAF-XC866*-2RRA 3V	3.3	—	4	8	Automotive
	SAF-XC866*-2RRI 3V	3.3	—	4	8	Industrial

¹⁾ Industrial is not for Automotive usage

²⁾ The flash memory (P-Flash and D-Flash) can be used for code or data.

Note: The asterisk (*) above denotes the device configuration letters from **Table 1**.

2 General Device Information

2.1 Block Diagram

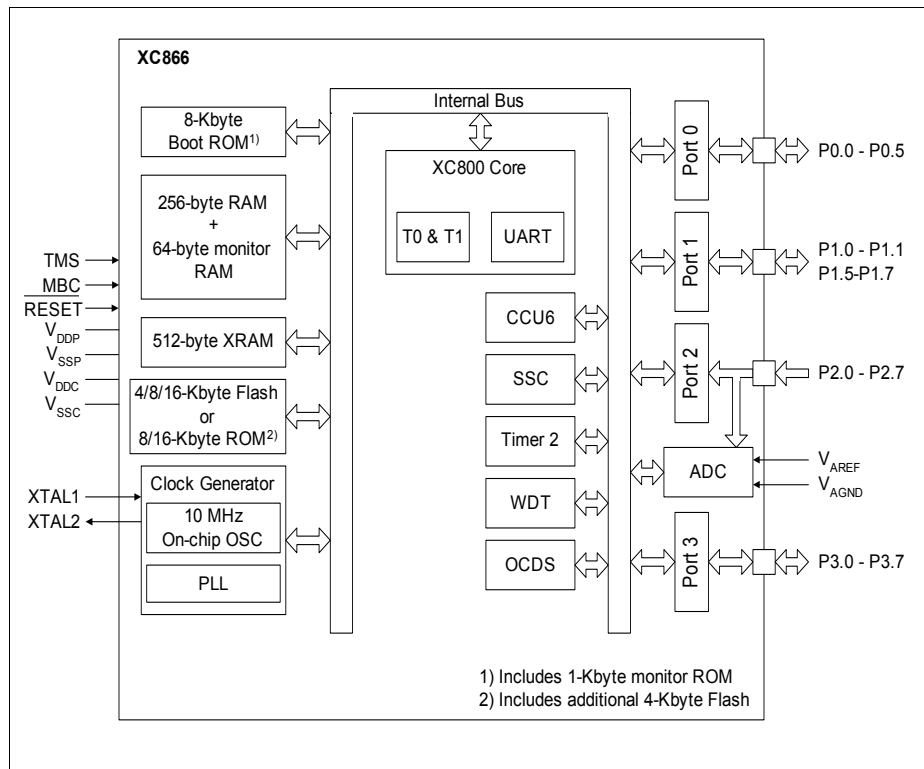


Figure 2 XC866 Block Diagram

2.3 Pin Configuration

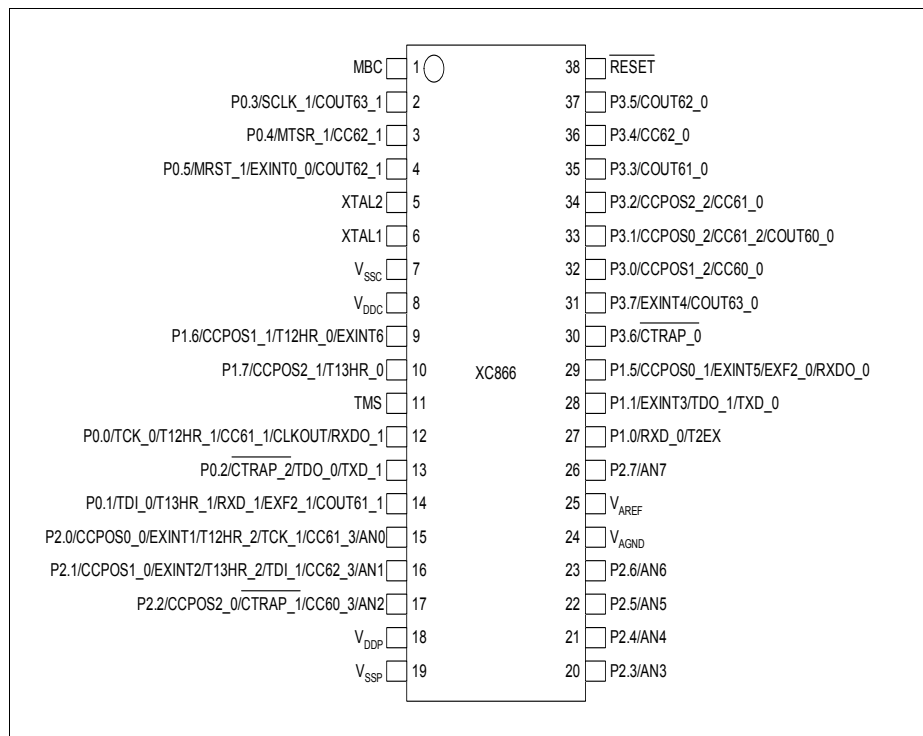


Figure 4 XC866 Pin Configuration, PG-TSSOP-38 Package (top view)

Functional Description

Field	Bits	Type	Description
OP	[7:6]	w	Operation 0X Manual page mode. The value of STNR is ignored and PAGE is directly written. 10 New page programming with automatic page saving. The value written to the bit positions of PAGE is stored. In parallel, the previous contents of PAGE are saved in the storage bit field STx indicated by STNR. 11 Automatic restore page action. The value written to the bit positions PAGE is ignored and instead, PAGE is overwritten by the contents of the storage bit field STx indicated by STNR.
0	3	r	Reserved Returns 0 if read; should be written with 0.

Functional Description

The Port SFRs can be accessed in the standard memory area (RMAP = 0).

Table 10 Port Register Overview

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
RMAP = 0										
B2 _H	PORT_PAGE Page Register for PORT	Reset: 00 _H	Bit Field	OP		STNR		0	PAGE	
			Type	w		w		r	rwh	
RMAP = 0, Page 0										
80 _H	P0_DATA P0 Data Register	Reset: 00 _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rwh	rwh	rwh	rwh	rwh
86 _H	P0_DIR P0 Direction Register	Reset: 00 _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rw	rw	rw	rw	rw
90 _H	P1_DATA P1 Data Register	Reset: 00 _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rwh	rwh	rwh	r		rwh	rwh
91 _H	P1_DIR P1 Direction Register	Reset: 00 _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rw	rw	rw	r		rw	rw
A0 _H	P2_DATA P2 Data Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rwh	rwh	rwh	rwh	rwh	rwh	rwh
A1 _H	P2_DIR P2 Direction Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
B0 _H	P3_DATA P3 Data Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rwh	rwh	rwh	rwh	rwh	rwh	rwh
B1 _H	P3_DIR P3 Direction Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
RMAP = 0, Page 1										
80 _H	P0_PUDEL P0 Pull-Up/Pull-Down Select Register	Reset: FF _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rw	rw	rw	rw	rw
86 _H	P0_PUDEN P0 Pull-Up/Pull-Down Enable Register	Reset: C4 _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rw	rw	rw	rw	rw
90 _H	P1_PUDEL P1 Pull-Up/Pull-Down Select Register	Reset: FF _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rw	rw	rw	r		rw	rw
91 _H	P1_PUDEN P1 Pull-Up/Pull-Down Enable Register	Reset: FF _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rw	rw	rw	r		rw	rw
A0 _H	P2_PUDEL P2 Pull-Up/Pull-Down Select Register	Reset: FF _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
A1 _H	P2_PUDEN P2 Pull-Up/Pull-Down Enable Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
B0 _H	P3_PUDEL P3 Pull-Up/Pull-Down Select Register	Reset: BF _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
B1 _H	P3_PUDEN P3 Pull-Up/Pull-Down Enable Register	Reset: 40 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw
RMAP = 0, Page 2										
80 _H	P0_ALTSEL0 P0 Alternate Select 0 Register	Reset: 00 _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rw	rw	rw	rw	rw
86 _H	P0_ALTSEL1 P0 Alternate Select 1 Register	Reset: 00 _H	Bit Field	0		P5	P4	P3	P2	P1 P0
			Type	r		rw	rw	rw	rw	rw
90 _H	P1_ALTSEL0 P1 Alternate Select 0 Register	Reset: 00 _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rw	rw	rw	r		rw	rw
91 _H	P1_ALTSEL1 P1 Alternate Select 1 Register	Reset: 00 _H	Bit Field	P7	P6	P5	0		P1	P0
			Type	rw	rw	rw	r		rw	rw
B0 _H	P3_ALTSEL0 P3 Alternate Select 0 Register	Reset: 00 _H	Bit Field	P7	P6	P5	P4	P3	P2	P1 P0
			Type	rw	rw	rw	rw	rw	rw	rw

Functional Description

Table 11 ADC Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
CA _H	ADC_RESR0L Result Register 0 Low Reset: 00 _H	Bit Field	RESULT[1:0]		0	VF	DRC	CHNR		
		Type	rh		r	rh	rh	rh		
CB _H	ADC_RESR0H Result Register 0 High Reset: 00 _H	Bit Field	RESULT[9:2]							
		Type	rh							
CC _H	ADC_RESR1L Result Register 1 Low Reset: 00 _H	Bit Field	RESULT[1:0]		0	VF	DRC	CHNR		
		Type	rh		r	rh	rh	rh		
CD _H	ADC_RESR1H Result Register 1 High Reset: 00 _H	Bit Field	RESULT[9:2]							
		Type	rh							
CE _H	ADC_RESR2L Result Register 2 Low Reset: 00 _H	Bit Field	RESULT[1:0]		0	VF	DRC	CHNR		
		Type	rh		r	rh	rh	rh		
CF _H	ADC_RESR2H Result Register 2 High Reset: 00 _H	Bit Field	RESULT[9:2]							
		Type	rh							
D2 _H	ADC_RESR3L Result Register 3 Low Reset: 00 _H	Bit Field	RESULT[1:0]		0	VF	DRC	CHNR		
		Type	rh		r	rh	rh	rh		
D3 _H	ADC_RESR3H Result Register 3 High Reset: 00 _H	Bit Field	RESULT[9:2]							
		Type	rh							
RMAP = 0, Page 3										
CA _H	ADC_RESRA0L Result Register 0, View A Low Reset: 00 _H	Bit Field	RESULT[2:0]			VF	DRC	CHNR		
		Type	rh			rh	rh	rh		
CB _H	ADC_RESRA0H Result Register 0, View A High Reset: 00 _H	Bit Field	RESULT[10:3]							
		Type	rh							
CC _H	ADC_RESRA1L Result Register 1, View A Low Reset: 00 _H	Bit Field	RESULT[2:0]			VF	DRC	CHNR		
		Type	rh			rh	rh	rh		
CD _H	ADC_RESRA1H Result Register 1, View A High Reset: 00 _H	Bit Field	RESULT[10:3]							
		Type	rh							
CE _H	ADC_RESRA2L Result Register 2, View A Low Reset: 00 _H	Bit Field	RESULT[2:0]			VF	DRC	CHNR		
		Type	rh			rh	rh	rh		
CF _H	ADC_RESRA2H Result Register 2, View A High Reset: 00 _H	Bit Field	RESULT[10:3]							
		Type	rh							
D2 _H	ADC_RESRA3L Result Register 3, View A Low Reset: 00 _H	Bit Field	RESULT[2:0]			VF	DRC	CHNR		
		Type	rh			rh	rh	rh		
D3 _H	ADC_RESRA3H Result Register 3, View A High Reset: 00 _H	Bit Field	RESULT[10:3]							
		Type	rh							
RMAP = 0, Page 4										
CA _H	ADC_RCR0 Result Control Register 0 Reset: 00 _H	Bit Field	VFCTR	WFR	0	IEN	0			DRCT R
		Type	rw	rw	r	rw	r			rw
CB _H	ADC_RCR1 Result Control Register 1 Reset: 00 _H	Bit Field	VFCTR	WFR	0	IEN	0			DRCT R
		Type	rw	rw	r	rw	r			rw
CC _H	ADC_RCR2 Result Control Register 2 Reset: 00 _H	Bit Field	VFCTR	WFR	0	IEN	0			DRCT R
		Type	rw	rw	r	rw	r			rw
CD _H	ADC_RCR3 Result Control Register 3 Reset: 00 _H	Bit Field	VFCTR	WFR	0	IEN	0			DRCT R
		Type	rw	rw	r	rw	r			rw
CE _H	ADC_VFCR Valid Flag Clear Register Reset: 00 _H	Bit Field	0				VFC3	VFC2	VFC1	VFC0
		Type	r				w	w	w	w
RMAP = 0, Page 5										

Functional Description

Table 14 SSC Register Overview

AB _H	SSC_CONH Control Register High <i>Programming Mode</i>	Reset: 00_H	Bit Field	EN	MS	0	AREN	BEN	PEN	REN	TEN
			Type	rw	rw	r	rw	rw	rw	rw	rw
	<i>Operating Mode</i>		Bit Field	EN	MS	0	BSY	BE	PE	RE	TE
			Type	rw	rw	r	rh	rwh	rwh	rwh	rwh
AC _H	SSC_TBL Transmitter Buffer Register Low	Reset: 00_H	Bit Field	TB_VALUE							
			Type	rw							
AD _H	SSC_RBL Receiver Buffer Register Low	Reset: 00_H	Bit Field	RB_VALUE							
			Type	rh							
AE _H	SSC_BRL Baudrate Timer Reload Register Low	Reset: 00_H	Bit Field	BR_VALUE[7:0]							
			Type	rw							
AF _H	SSC_BRH Baudrate Timer Reload Register High	Reset: 00_H	Bit Field	BR_VALUE[15:8]							
			Type	rw							

The OCDS SFRs can be accessed in the mapped memory area (RMAP = 1).

Table 15 OCDS Register Overview

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
RMAP = 1										
E9 _H	MMCR2 Monitor Mode Control Register 2 Reset: 00_H	Bit Field	EXBC_P	EXBC	MBCO_N_P	MBCO_N	MMEP_P	MMEP	MMODE	JENA
		Type	w	rw	w	rwh	w	rwh	rh	rh
F1 _H	MMCR Monitor Mode Control Register Reset: 00_H	Bit Field	MEXIT_P	MEXIT	MSTEP_P	MSTEP	MRAM_S_P	MRAM_S	TRF	RRF
		Type	w	rwh	w	rw	w	rwh	rh	rh
F2 _H	MMSR Monitor Mode Status Register Reset: 00_H	Bit Field	MBCA_M	MBCIN	EXBF	SWBF	HWB3_F	HWB2_F	HWB1_F	HWB0_F
		Type	rw	rh	rwh	rwh	rwh	rwh	rwh	rwh
F3 _H	MMBPCR BreakPoints Control Register Reset: 00_H	Bit Field	SWBC	HWB3C		HWB2C		HWB1_C	HWB0C	
		Type	rw	rw		rw		rw	rw	
F4 _H	MMICR Monitor Mode Interrupt Control Register Reset: 00_H	Bit Field	DVECT	DRETR	0		MMUIE_P	MMUIE	RRIE_P	RRIE
		Type	rwh	rwh	r		w	rw	w	rw
F5 _H	MMDR Monitor Mode Data Register Reset: 00_H <i>Receive</i> <i>Transmit</i>	Bit Field	MMRR							
		Type	rh							
		Bit Field	MMTR							
		Type	w							
F6 _H	HWBPSR Hardware Breakpoints Select Register Reset: 00_H	Bit Field	0			BPSEL_P	BPSEL			
		Type	r			w	rw			
F7 _H	HWBPDR Hardware Breakpoints Data Register Reset: 00_H	Bit Field	HWBPxx							
		Type	rw							

3.3 Flash Memory

The Flash memory provides an embedded user-programmable non-volatile memory, allowing fast and reliable storage of user code and data. It is operated from a single 2.5 V supply from the Embedded Voltage Regulator (EVR) and does not require additional programming or erasing voltage. The sectorization of the Flash memory allows each sector to be erased independently.

Features

- In-System Programming (ISP) via UART
- In-Application Programming (IAP)
- Error Correction Code (ECC) for dynamic correction of single-bit errors
- Background program and erase operations for CPU load minimization
- Support for aborting erase operation
- Minimum program width¹⁾ of 32-byte for D-Flash and 32-byte for P-Flash
- 1-sector minimum erase width
- 1-byte read access
- Flash is delivered in erased state (read all zeros)
- Operating supply voltage: 2.5 V \pm 7.5 %
- Read access time: $3 \times t_{\text{CCLK}} = 112.5 \text{ ns}^2)$
- Program time: $209440 / f_{\text{SYS}} = 2.6 \text{ ms}^3)$
- Erase time: $8175360 / f_{\text{SYS}} = 102 \text{ ms}^3)$

¹⁾ P-Flash: 32-byte wordline can only be programmed once, i.e., one gate disturb allowed.
D-Flash: 32-byte wordline can be programmed twice, i.e., two gate disturbs allowed.

²⁾ $f_{\text{SYS}} = 80 \text{ MHz} \pm 7.5\%$ ($f_{\text{CCLK}} = 26.7 \text{ MHz} \pm 7.5\%$) is the maximum frequency range for Flash read access.

³⁾ $f_{\text{SYS}} = 80 \text{ MHz} \pm 7.5\%$ is the only frequency range for Flash programming and erasing. f_{SYSmin} is used for obtaining the worst case timing.

Functional Description

Table 16 shows the Flash data retention and endurance targets.

Table 16 Flash Data Retention and Endurance (Operating Conditions apply)

Retention	Endurance ¹⁾	Size	Remarks
Program Flash			
20 years	1,000 cycles	up to 16 Kbytes ²⁾	for 16-Kbyte Variant
20 years	1,000 cycles	up to 8 Kbytes ²⁾	for 8-Kbyte Variant
20 years	1,000 cycles	up to 4 Kbytes ²⁾	for 4-Kbyte Variant
Data Flash			
20 years	1,000 cycles	4 Kbytes	
5 years	10,000 cycles	1 Kbyte	
2 years	70,000 cycles	512 bytes	
2 years	100,000 cycles	128 bytes	

¹⁾ One cycle refers to the programming of all wordlines in a sector and erasing of sector. The Flash endurance data specified in **Table 16** is valid only if the following conditions are fulfilled:

- the maximum number of erase cycles per Flash sector must not exceed 100,000 cycles.
- the maximum number of erase cycles per Flash bank must not exceed 300,000 cycles.
- the maximum number of program cycles per Flash bank must not exceed 2,500,000 cycles.

²⁾ If no Flash is used for data, the Program Flash size can be up to the maximum Flash size available in the device variant. Having more Data Flash will mean less Flash is available for Program Flash.

3.3.1 Flash Bank Sectorization

The XC866 product family offers four Flash devices with either 8 Kbytes or 16 Kbytes of embedded Flash memory. These Flash memory sizes are made up of two or four 4-Kbyte Flash banks, respectively. Each Flash device consists of Program Flash (P-Flash) bank(s) and a single Data Flash (D-Flash) bank with different sectorization shown in **Figure 11**. Both types can be used for code and data storage. The label “Data” neither implies that the D-Flash is mapped to the data memory region, nor that it can only be used for data storage. It is used to distinguish the different Flash bank sectorizations. The XC866 ROM devices offer a single 4-Kbyte D-Flash bank.

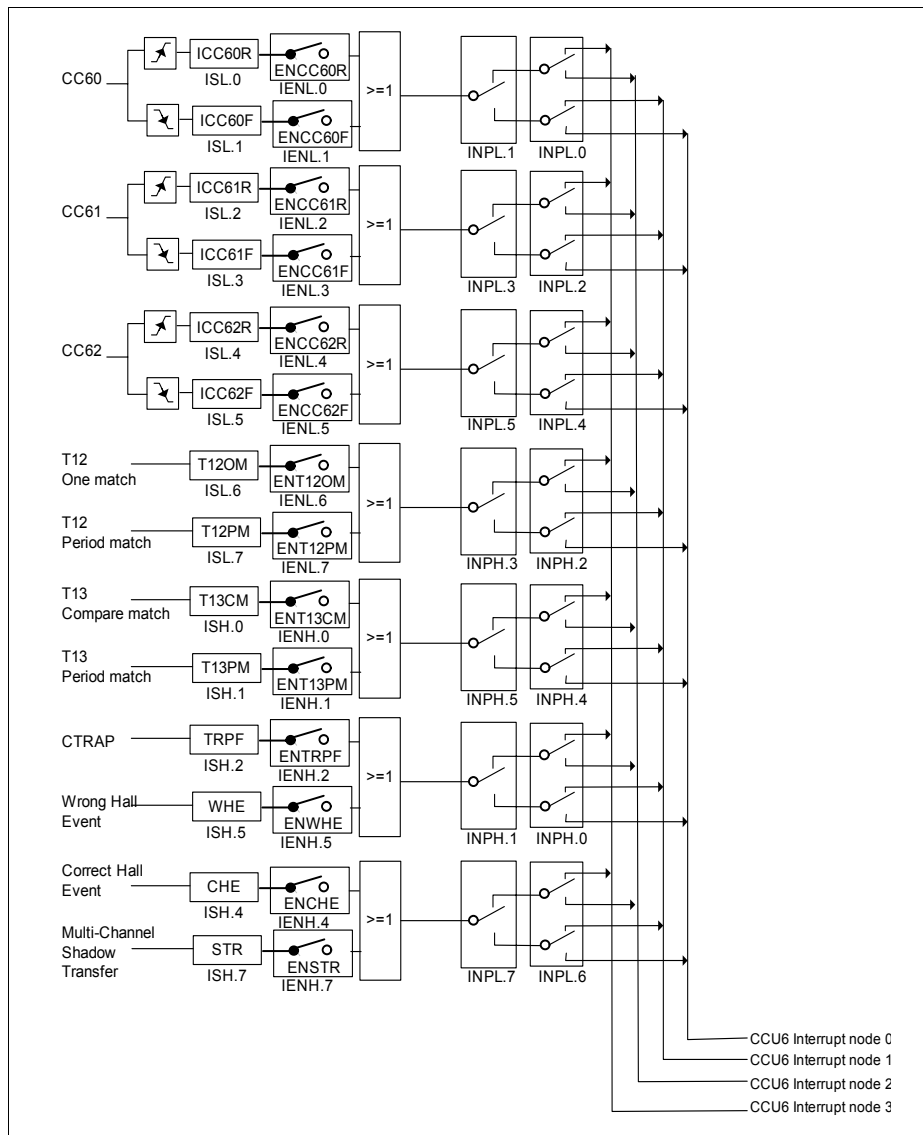


Figure 17 Interrupt Request Sources (Part 4)

3.4.2 Interrupt Source and Vector

Each interrupt source has an associated interrupt vector address. This vector is accessed to service the corresponding interrupt source request. The interrupt service of each interrupt source can be individually enabled or disabled via an enable bit. The assignment of the XC866 interrupt sources to the interrupt vector addresses and the corresponding interrupt source enable bits are summarized in **Table 17**.

Table 17 Interrupt Vector Addresses

Interrupt Source	Vector Address	Assignment for XC866	Enable Bit	SFR
NMI	0073 _H	Watchdog Timer NMI	NMIWDT	NMICON
		PLL NMI	NMIPLL	
		Flash NMI	NMIFLASH	
		VDDC Prewarning NMI	NMIVDD	
		VDDP Prewarning NMI	NMIVDDP	
		Flash ECC NMI	NMIECC	
XINTR0	0003 _H	External Interrupt 0	EX0	IEN0
XINTR1	000B _H	Timer 0	ET0	
XINTR2	0013 _H	External Interrupt 1	EX1	
XINTR3	001B _H	Timer 1	ET1	
XINTR4	0023 _H	UART	ES	
XINTR5	002B _H	T2	ET2	
		Fractional Divider (Normal Divider Overflow)		
		LIN		

Functional Description
Table 17 Interrupt Vector Addresses (cont'd)

XINTR6	0033 _H	ADC	EADC	IEN1
XINTR7	003B _H	SSC	ESSC	
XINTR8	0043 _H	External Interrupt 2	EX2	
XINTR9	004B _H	External Interrupt 3	EXM	
		External Interrupt 4		
		External Interrupt 5		
		External Interrupt 6		
XINTR10	0053 _H	CCU6 INP0	ECCIP0	
XINTR11	005B _H	CCU6 INP1	ECCIP1	
XINTR12	0063 _H	CCU6 INP2	ECCIP2	
XINTR13	006B _H	CCU6 INP3	ECCIP3	

3.10 Watchdog Timer

The Watchdog Timer (WDT) provides a highly reliable and secure way to detect and recover from software or hardware failures. The WDT is reset at a regular interval that is predefined by the user. The CPU must service the WDT within this interval to prevent the WDT from causing an XC866 system reset. Hence, routine service of the WDT confirms that the system is functioning properly. This ensures that an accidental malfunction of the XC866 will be aborted in a user-specified time period. In debug mode, the WDT is suspended and stops counting. Therefore, there is no need to refresh the WDT during debugging.

Features:

- 16-bit Watchdog Timer
- Programmable reload value for upper 8 bits of timer
- Programmable window boundary
- Selectable input frequency of $f_{PCLK}/2$ or $f_{PCLK}/128$
- Time-out detection with NMI generation and reset prewarning activation (after which a system reset will be performed)

The WDT is a 16-bit timer incremented by a count rate of $f_{PCLK}/2$ or $f_{PCLK}/128$. This 16-bit timer is realized as two concatenated 8-bit timers. The upper 8 bits of the WDT can be preset to a user-programmable value via a watchdog service access in order to modify the watchdog expire time period. The lower 8 bits are reset on each service access. **Figure 27** shows the block diagram of the WDT unit.

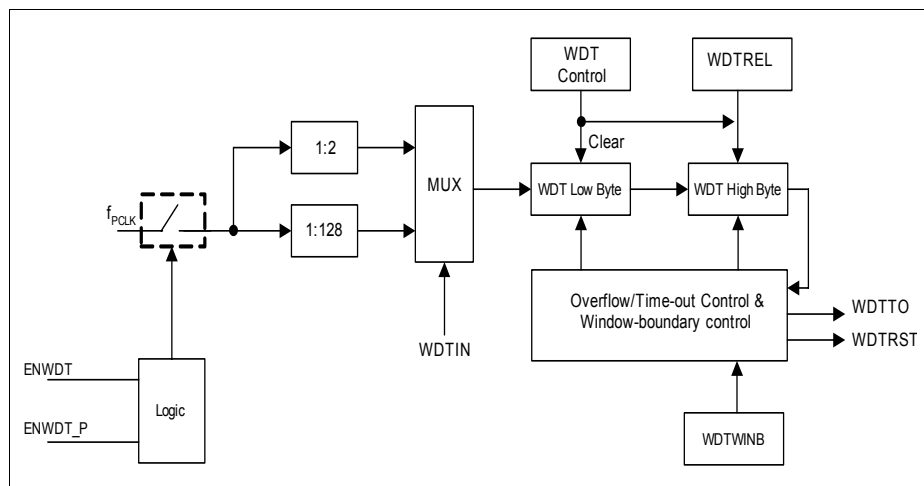


Figure 27 WDT Block Diagram

Functional Description

If the WDT is not serviced before the timer overflow, a system malfunction is assumed. As a result, the WDT NMI is triggered (assert WDTTO) and the reset prewarning is entered. The prewarning period lasts for 30_H count, after which the system is reset (assert WDTRST).

The WDT has a “programmable window boundary” which disallows any refresh during the WDT’s count-up. A refresh during this window boundary constitutes an invalid access to the WDT, causing the reset prewarning to be entered but without triggering the WDT NMI. The system will still be reset after the prewarning period is over. The window boundary is from 0000_H to the value obtained from the concatenation of WDTWINB and 00_H.

After being serviced, the WDT continues counting up from the value (<WDTREL> * 2⁸). The time period for an overflow of the WDT is programmable in two ways:

- the input frequency to the WDT can be selected to be either $f_{PCLK}/2$ or $f_{PCLK}/128$
- the reload value WDTREL for the high byte of WDT can be programmed in register WDTREL

The period, P_{WDT} , between servicing the WDT and the next overflow can be determined by the following formula:

$$P_{WDT} = \frac{2^{(1 + WDTIN \times 6)} \times (2^{16} - WDTREL \times 2^8)}{f_{PCLK}}$$

If the Window-Boundary Refresh feature of the WDT is enabled, the period P_{WDT} between servicing the WDT and the next overflow is shortened if WDTWINB is greater than WDTREL, see **Figure 28**. This period can be calculated using the same formula by replacing WDTREL with WDTWINB. For this feature to be useful, WDTWINB should not be smaller than WDTREL.

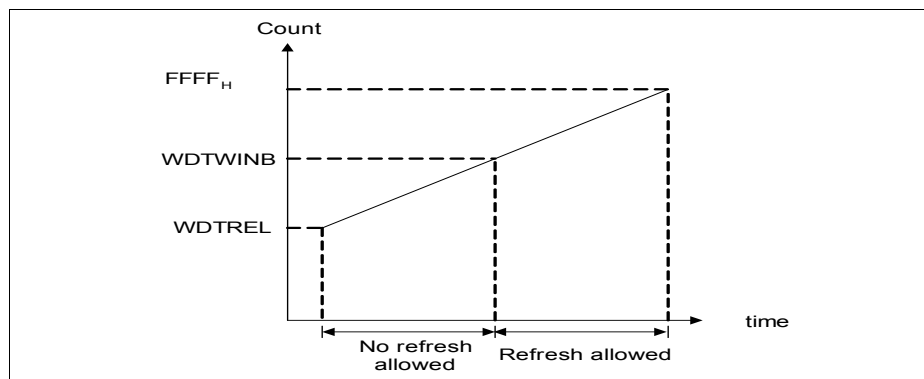


Figure 28 WDT Timing Diagram

3.14 High-Speed Synchronous Serial Interface

The High-Speed Synchronous Serial Interface (SSC) supports full-duplex and half-duplex synchronous communication. The serial clock signal can be generated by the SSC internally (master mode), using its own 16-bit baud-rate generator, or can be received from an external master (slave mode). Data width, shift direction, clock polarity and phase are programmable. This allows communication with SPI-compatible devices or devices using other synchronous serial interfaces.

Features:

- Master and slave mode operation
 - Full-duplex or half-duplex operation
- Transmit and receive buffered
- Flexible data format
 - Programmable number of data bits: 2 to 8 bits
 - Programmable shift direction: LSB or MSB shift first
 - Programmable clock polarity: idle low or high state for the shift clock
 - Programmable clock/data phase: data shift with leading or trailing edge of the shift clock
- Variable baud rate
- Compatible with Serial Peripheral Interface (SPI)
- Interrupt generation
 - On a transmitter empty condition
 - On a receiver full condition
 - On an error condition (receive, phase, baud rate, transmit error)

Functional Description
Table 31 JTAG ID Summary

ROM	XC866L-4RR	1013 9083 _H
	XC866-4RR	1013 9083 _H
	XC866L-2RR	1013 9083 _H
	XC866-2RR	1013 9083 _H

3.20 Identification Register

The XC866 identity register is located at Page 1 of address B3_H.

ID
Identity Register
Reset Value: 0000 0010_B

7	6	5	4	3	2	1	0
PRODID					VERID		
r					r		

Field	Bits	Type	Description
VERID	[2:0]	r	Version ID 010 _B
PRODID	[7:3]	r	Product ID 00000 _B

Electrical Parameters

Table 36 ADC Characteristics (Operating Conditions apply; $V_{DDP} = 5V$ Range)

Parameter	Symbol	Limit Values			Unit	Test Conditions/ Remarks
		min.	typ .	max.		
Switched capacitance at the analog voltage inputs	C_{AINSW} CC	–	5	7	pF	2)4)
Input resistance of the reference input	R_{AREF} CC	–	1	2	k Ω	2)
Input resistance of the selected analog channel	R_{AIN} CC	–	1	1.5	k Ω	2)

1) TUE is tested at $V_{AREF} = 5.0 V$, $V_{AGND} = 0 V$, $V_{DDP} = 5.0 V$.

2) Not subject to production test, verified by design/characterization.

3) This represents an equivalent switched capacitance. This capacitance is not switched to the reference voltage at once. Instead of this, smaller capacitances are successively switched to the reference voltage.

4) The sampling capacity of the conversion C-Network is pre-charged to $V_{AREF}/2$ before connecting the input to the C-Network. Because of the parasitic elements, the voltage measured at ANx is lower than $V_{AREF}/2$.

4.3.3 Power-on Reset and PLL Timing

Table 42 Power-On Reset and PLL Timing (Operating Conditions apply)

Parameter	Symbol	Limit Values			Unit	Test Conditions
		min.	typ.	max.		
Pad operating voltage	V_{PAD} CC	2.3	–	–	V	
On-Chip Oscillator start-up time	t_{OSCST} CC	–	–	500	ns	
Flash initialization time	t_{FINIT} CC	–	160	–	μ s	
\overline{RESET} hold time ¹⁾	t_{RST} SR	–	500	–	μ s	V_{DDP} rise time (10% – 90%) $\leq 500\mu$ s
PLL lock-in in time	t_{LOCK} CC	–	–	200	μ s	
PLL accumulated jitter	D_P	–	–	0.7	ns	²⁾

1) \overline{RESET} signal has to be active (low) until V_{DDC} has reached 90% of its maximum value (typ. 2.5V).

2) PLL lock at 80 MHz using a 4 MHz external oscillator. The PLL Divider settings are K = 2, N = 40 and P = 1.

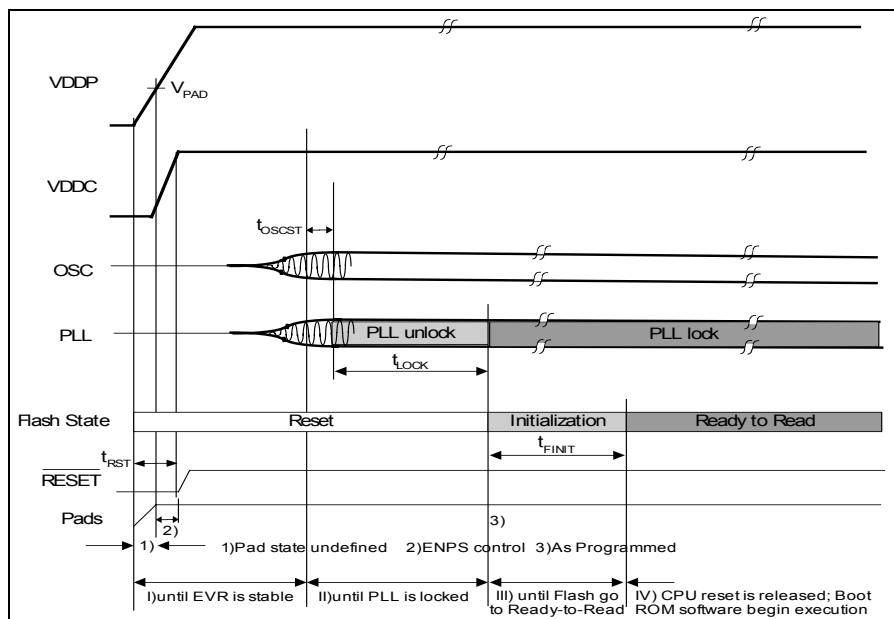







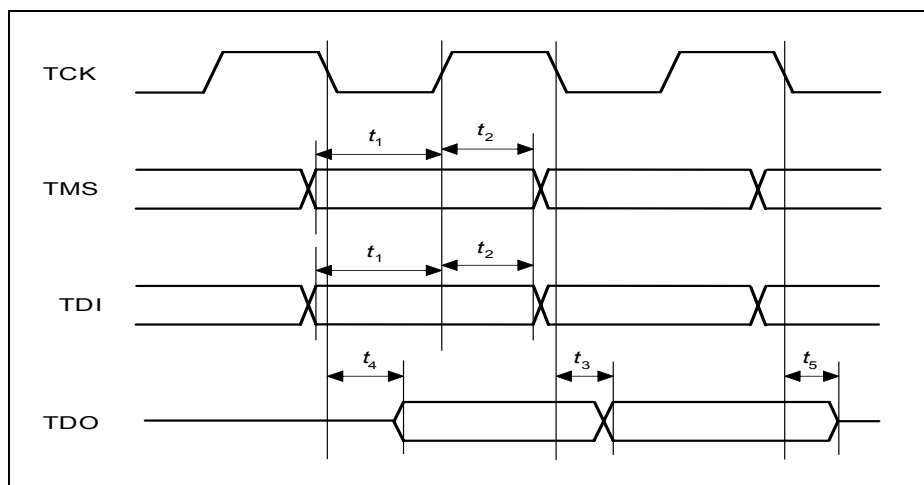


Figure 42 Power-on Reset Timing

Electrical Parameters

Table 45 JTAG Timing (Operating Conditions apply; $C_L = 50$ pF)

Parameter	Symbol		Limits		Unit
			min	max	
TMS setup to TCK 	t_1	SR	8.0	–	ns
TMS hold to TCK 	t_2	SR	5.0	–	ns
TDI setup to TCK 	t_1	SR	11.0	–	ns
TDI hold to TCK 	t_2	SR	6.0	–	ns
TDO valid output from TCK 	t_3	CC	–	23	ns
TDO high impedance to valid output from TCK 	t_4	CC	–	26	ns
TDO valid output to high impedance from TCK 	t_5	CC	–	18	ns


Figure 44 JTAG Timing